NTMS4N01R2

Power MOSFET
4.2 Amps, 20 Volts
N−Channel Enhancement−Mode
Single SO−8 Package

Features

- High Density Power MOSFET with Ultra Low $R_{DS(on)}$ Providing Higher Efficiency
- Miniature SO−8 Surface Mount Package Saving Board Space; Mounting Information for the SO−8 Package is Provided
- I_{DSS} Specified at Elevated Temperature
- Drain−to−Source Avalanche Energy Specified
- Diode Exhibits High Speed, Soft Recovery
- Pb−Free Package is Available

Applications

- Power Management in Portable and Battery−Powered Products, i.e.: Computers, Printers, PCMCIA Cards, Cellular & Cordless Telephones

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage	V_{DSS}	20	V
Drain−to−Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	20	V
Gate−to−Source Voltage − Continuous	V_{GS}	±10	V
Thermal Resistance, Junction−to−Ambient (Note 1) Total Power Dissipation @ T_A = 25°C Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D I_{DM}	50 2.5 5.9 4.7 25	°C/W W A A A
Thermal Resistance, Junction−to−Ambient (Note 2) Total Power Dissipation @ T_A = 25°C Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D I_{DM}	100 1.25 4.2 3.3 20	°C/W W A A A
Thermal Resistance, Junction−to−Ambient (Note 3) Total Power Dissipation @ T_A = 25°C Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D I_{DM}	162 0.77 3.3 2.6 15	°C/W W A A A
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
Single Pulse Drain−to−Source Avalanche Energy − Starting T_J = 25°C (V_{DD} = 20 Vdc, V_{GS} = 5.0 Vdc, Peak I_L = 7.5 Apk, L = 6 mH, R_G = 25 Ω)	E_{AS}	169	mJ
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 10 seconds	T_L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Mounted onto a 2″ square FR−4 Board (1″ sq. 2 oz Cu 0.06″ thick single sided), t ≤ 10 seconds.
2. Mounted onto a 2″ square FR−4 Board (1″ sq. 2 oz Cu 0.06″ thick single sided), t = steady state.
3. Minimum FR−4 or G−10 PCB, t = Steady State.
4. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

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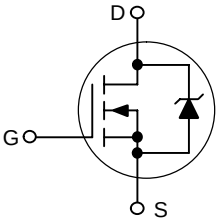
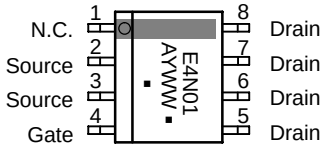
4.2 AMPERES, 20 VOLTS
0.045 Ω @ V_{GS} = 4.5 V

Single N−Channel



SO−8
CASE 751
STYLE 13

MARKING DIAGRAM AND PIN ASSIGNMENT



Top View

E4N01 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTMS4N01R2	SO−8	2500 / Tape & Reel
NTMS4N01R2G	SO−8 (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted) (Note 5)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain−to−Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 250 μAdc) Temperature Coefficient (Positive)	$V_{(BR)DSS}$	 20 −	 − 20	 − −	Vdc mV/°C
Zero Gate Voltage Drain Current (V_{DS} = 12 Vdc, V_{GS} = 0 Vdc, T_J = 25°C) (V_{DS} = 12 Vdc, V_{GS} = 0 Vdc, T_J = 125°C) (V_{DS} = 20 Vdc, V_{GS} = 0 Vdc, T_J = 25°C)	I_{DSS}	 − − −	 − − 0.2	 1.0 10 −	μAdc
Gate−Body Leakage Current (V_{GS} = +10 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	−	−	100	nAdc
Gate−Body Leakage Current (V_{GS} = −10 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	−	−	−100	nAdc
ON CHARACTERISTICS					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μAdc) Temperature Coefficient (Negative)	$V_{GS(th)}$	 0.6 −	 0.95 −3.0	 1.2 −	Vdc mV/°C
Static Drain−to−Source On−State Resistance (V_{GS} = 4.5 Vdc, I_D = 4.2 Adc) (V_{GS} = 2.7 Vdc, I_D = 2.1 Adc) (V_{GS} = 2.5 Vdc, I_D = 2.0 Adc)	$R_{DS(on)}$	 − − −	 0.030 0.035 0.037	 0.04 0.05 −	Ω
Forward Transconductance (V_{DS} = 2.5 Vdc, I_D = 2.0 Adc)	g_{FS}	−	10	−	Mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	C_{iss}	−	870	1200	pF
Output Capacitance	C_{oss}	−	260	400	
Reverse Transfer Capacitance	C_{rss}	−	60	100	

(V_{DS} = 10 Vdc, V_{GS} = 0 Vdc, f = 1.0 MHz)

SWITCHING CHARACTERISTICS (Notes 6 & 7)

Turn−On Delay Time					

(V_{DD} = 12 Vdc, I_D = 4.2 Adc, V_{GS} = 4.5 Vdc, R_G = 2.3 Ω)

T101(otal Gate Chargme)]TJET59.76 010.36 0.59999 15.36 ref59.76 15126 133.92 0.60001 refBT8 0 0 8 344.442990.36 Tm0 Tw((V)Tj6.5 0 0 6.5 552408

ime −

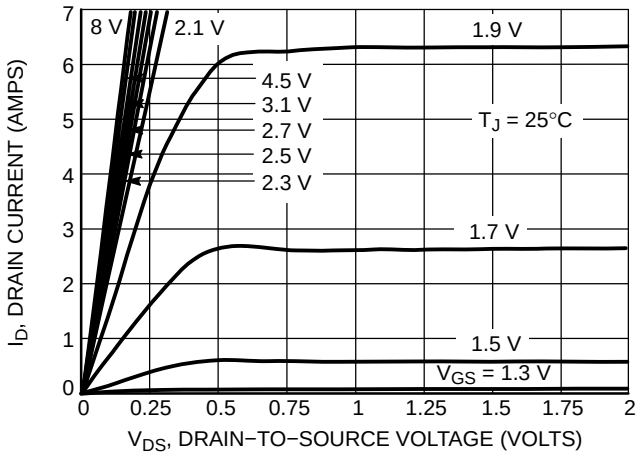


Figure 1. On−Region Characteristics

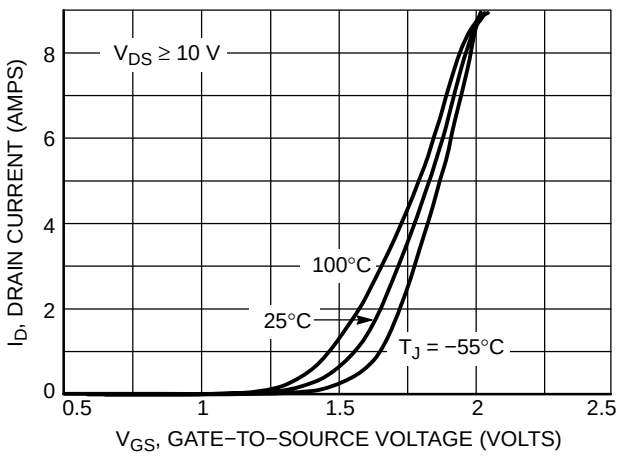


Figure 2. Transfer Characteristics

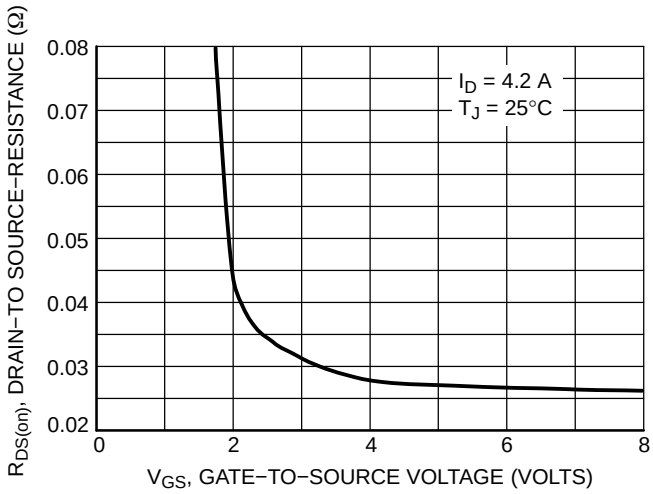


Figure 3. On−Resistance versus Gate−To−Source Voltage

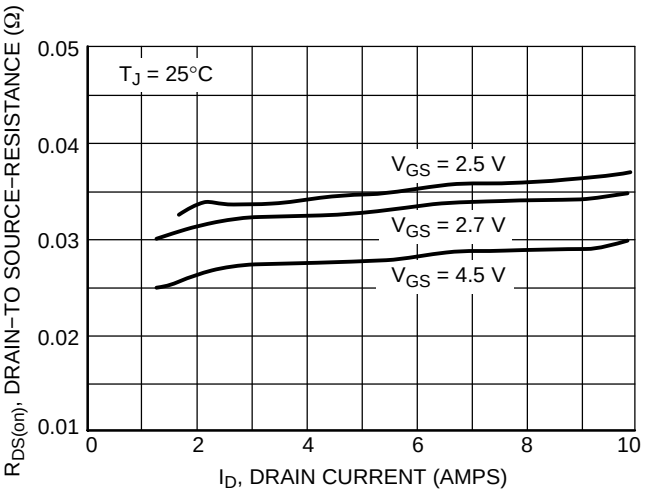


Figure 4. On-Resistance versus Drain Current and Gate Voltage

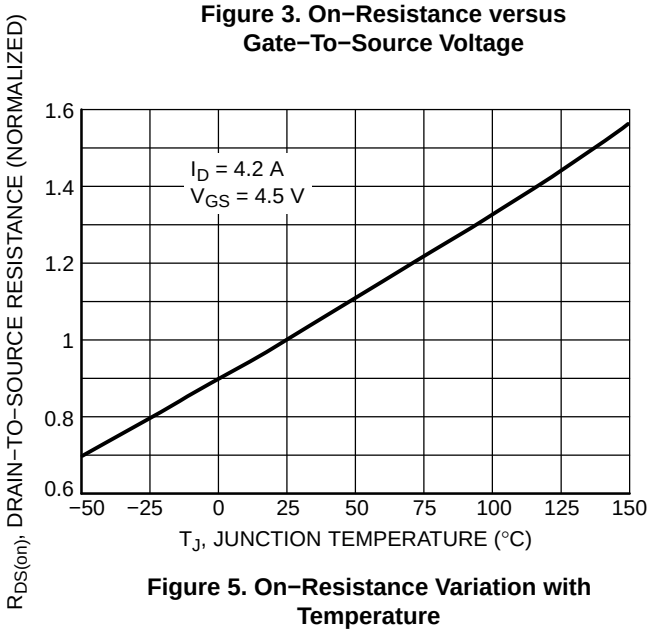


Figure 5. On−Resistance Variation with Temperature

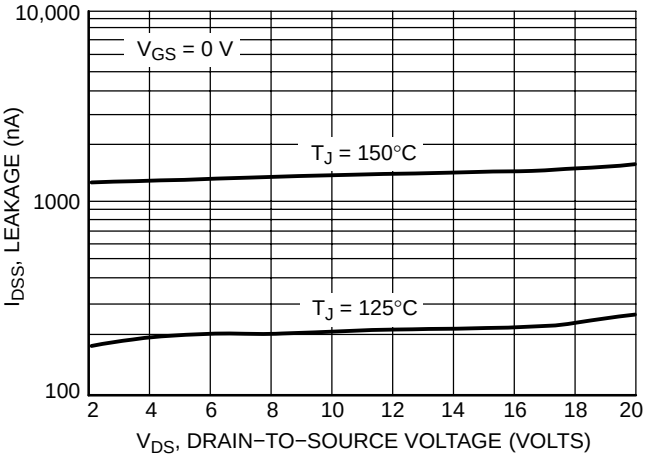


Figure 6. Drain−To−Source Leakage Current versus Voltage

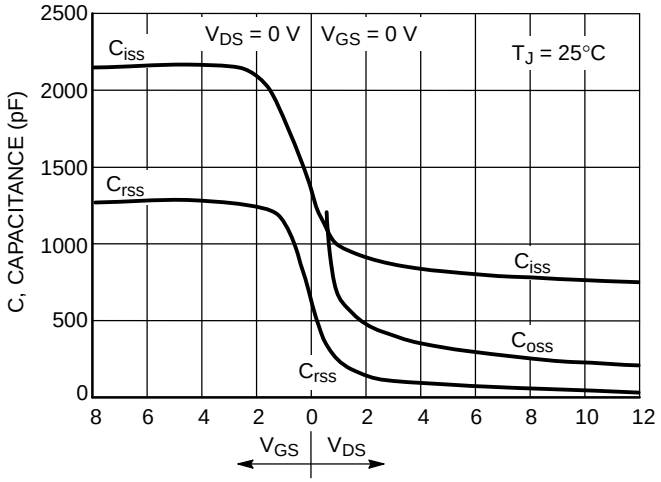


Figure 7. Capacitance Variation

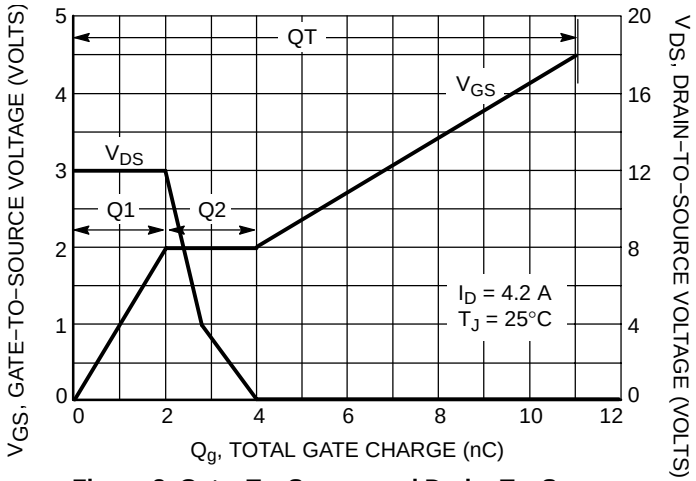


Figure 8. Gate−To−Source and Drain−To−Source Voltage versus Total Charge

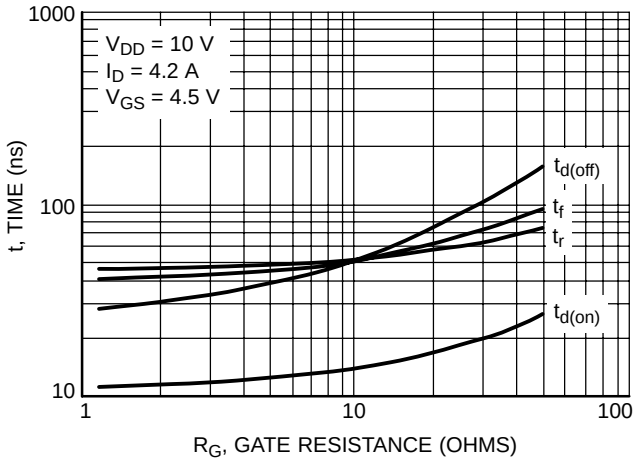


Figure 9. Resistive Switching Time Variation versus Gate Resistance

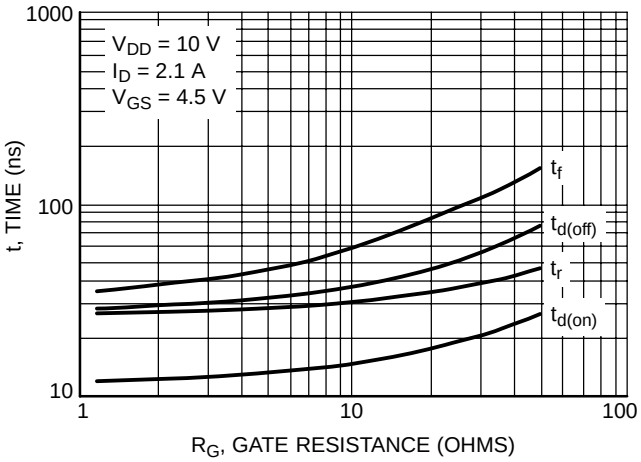


Figure 10. Resistive Switching Time Variation versus Gate Resistance

DRAIN−TO−SOURCE DIODE CHARACTERISTICS

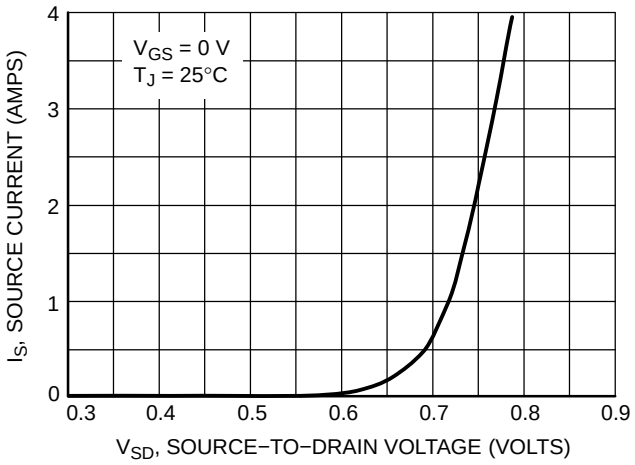


Figure 11. Diode Forward Voltage versus Current

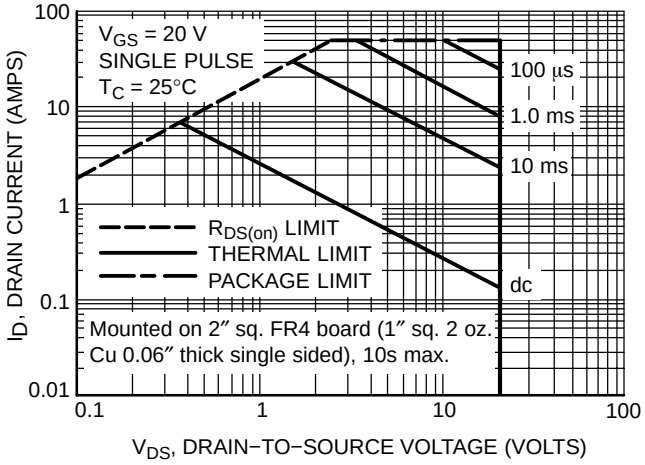


Figure 12. Maximum Rated Forward Biased Safe Operating Area

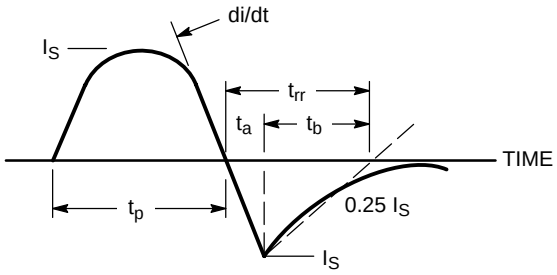


Figure 13. Diode Reverse Recovery Waveform

TYPICAL ELECTRICAL CHARACTERISTICS

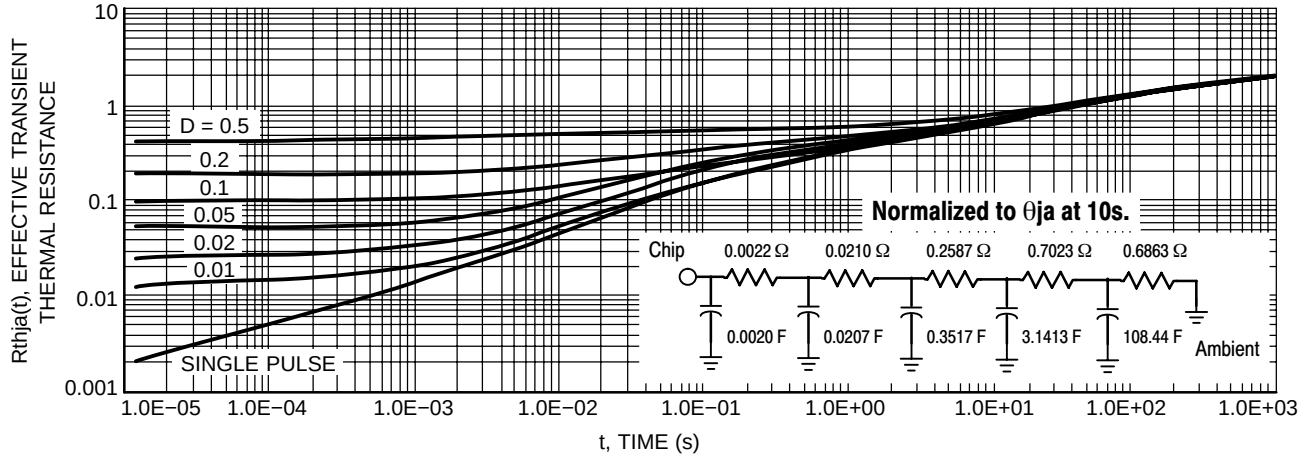
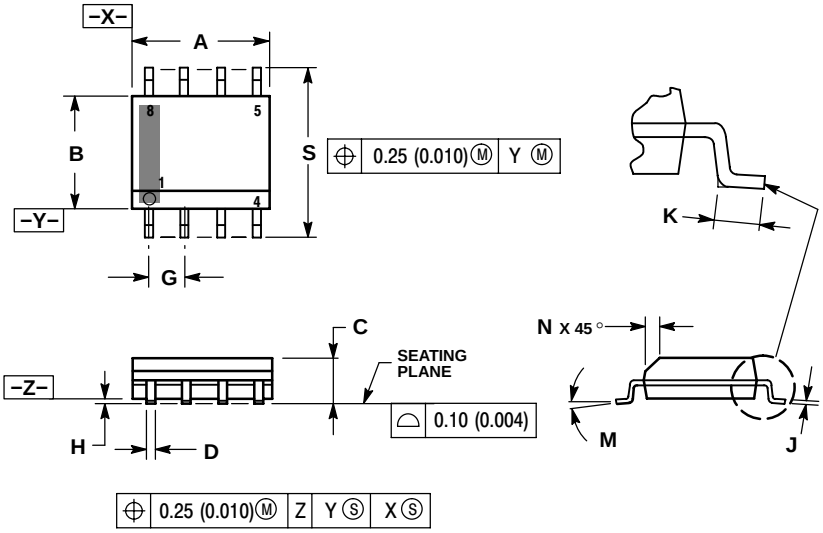


Figure 14. Thermal Response

PACKAGE DIMENSIONS

SOIC−8 NB
CASE 751−07
ISSUE AG

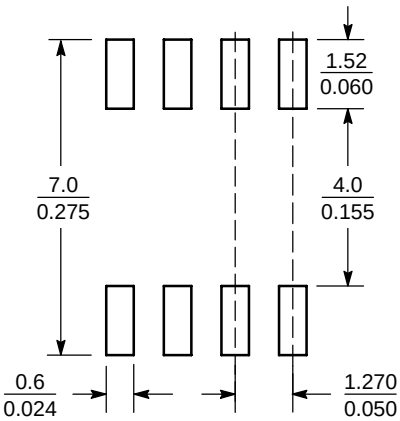


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

SOLDERING FOOTPRINT*



SCALE 6:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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